

C1  
a +  
and cover the border of the wafer surface other than the tapered face and thus not only the effective area of the wafer surface adapted for epitaxial layer formation can be increased but also there is no danger of a reaction product depositing on the area covering the periphery of the opening flange and thus causing contamination.

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Please replace paragraph [0021] with the following:

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C2  
In fact, while the use of two jaws is sufficient, if it is desired to simply hold the semiconductor wafer in place, such two-point support causes the wafer to tend to bend under its own weight and this trend is particularly manifest in the case of wafers of large diameters. Therefore, the wafer holder of the present invention is constructed so as to include at least three jaws. Considering from the design and production point of view, it is convenient to use a construction including three jaws or the previously mentioned construction having four jaws. Of course, it is possible to include five or more jaws and in any case the jaws are arranged at equal angular intervals along the holder periphery.

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Please replace paragraph [0024] with the following:

C3  
Fig. 1 is a schematic front view showing, as seen from the wafer back surface side, the interior of the chamber of an epitaxial growth furnace according to an embodiment of the present invention.

Please replace paragraph [0025] with the following:

C4  
Fig. 2 is a longitudinal sectional view showing the chamber interior of Fig. 1 as seen from the lateral side.

Please replace paragraph [0026] with the following:

C5  
Figs. 3a and 3b show the construction of a wafer holder used in the epitaxial growth furnace of Fig. 1, in which Fig. 3a is its plan view as seen from the back side and Fig. 3b is its cross-sectional view.

Please replace paragraph [0027] with the following:

C6  
Figs. 4a to 4c show the construction of the jaw actuating means in the wafer holder of Figs. 3a and 3b, in which Fig. 4a is a partial enlarged plan view as seen from the holder back side, Fig. 4b is a partial cross-sectional view, and Fig. 4c is an enlarged cross-sectional view of the jaw and the associated parts.

Please replace paragraph [0029] with the following:

c1 In the epitaxial growth furnace of the present embodiment, a pair of substantially cylindrical drum-type susceptors 2 are rotatably supported within a chamber 1 as shown in the schematic front view of Fig. 1 showing the interior of the chamber as seen from the back surface side of a semiconductor wafer and the central sectional view of Fig. 2 showing the chamber as seen from the lateral side.

Please replace paragraph [0032] with the following:

c8 Figs. 3a and 3b show the construction of the wafer holder 11 used in the epitaxial growth furnace of the present embodiment, in which Fig. 3a is a plan view as seen from the back side and Fig. 3b is a cross-sectional view. Figs. 4a to 4c show the spring-type actuating means of the wafer holder 11, with Fig. 4a showing a partial enlarged plan view as seen from the back side, Fig. 4b showing a partial sectional view of the actuating means, and Fig. 4c showing a schematic view useful for explaining the operation of the jaw.